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			U.S. PA	TENT DOCUMENTS					
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m		5,539,217	07/23/1996	Edmond et al.					
1		5,742,076	04/21/1998	Sridevan et al.					
		5,925,895	07/20/1999	Sriram et al.					
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dm		Nemati et on VLSI Te	Nemati et al, "A Novel High Density, Low Voltage SRAM Cell with a Vertical NDR Device", on VLSI Technology Digest of Technical Papers, IEEE, pages 66-67, 1998.						
dn			Nemati et al, "A Novel Thyristor-based SRAM Cell (T-RAM) for High Speed, Low-Voltage, Gi Memories", IEDM 1999, 283-286						
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